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Analysis of Stochastic Effect in Line-and-Space Resist Patterns Fabricated by Extreme Ultraviolet Lithography

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#	Paper	IF	Citations
75	Effect of Initial Dispersion of Protected Units on Line Edge Roughness of Chemically Amplified Extreme Ultraviolet Resists. *Journal of Photopolymer Science and Technology = [Fotoporima Konwakai Shi]*, **2013**, 26, 643-648	0.7	11
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